# Medium Power Thyristors (Stud Version), 10 A

TO-208AA (TO-48)

## FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dI/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V $V_{DRM}/V_{RRM}$
- RoHS compliant
- Designed and qualified for industrial and consumer level

RoHS COMPLIANT

## TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

| PRODUCT SUMMARY | |
|---|---|
| $I_{T(AV)}$ | 10 A |

| MAJOR RATINGS AND CHARACTERISTICS | | | |
|---|---|---|---|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS |
| $I_{T(AV)}$ | | 10 | A |
| | $T_C$ | 85 | °C |
| $I_{T(RMS)}$ | | 25 | A |
| $I_{TSM}$ | 50 Hz | 225 | A |
| | 60 Hz | 240 | |
| $I^2t$ | 50 Hz | 255 | $A^2s$ |
| | 60 Hz | 233 | |
| $V_{DRM}/V_{RRM}$ | | 100 to 1200 | V |
| $t_q$ | Typical | 110 | µs |
| $T_J$ | | - 65 to 125 | °C |

## ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | |
|---|---|---|---|---|
| TYPE NUMBER | VOLTAGE CODE | $V_{DRM}/V_{RRM}$, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE (1) V | $V_{RSM}$, MAXIMUM NON-REPETITIVE PEAK VOLTAGE (2) V | $I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA |
| 10RIA | 10 | 100 | 150 | 20 |
| | 20 | 200 | 300 | 10 |
| | 40 | 400 | 500 | |
| | 60 | 600 | 700 | |
| | 80 | 800 | 900 | |
| | 100 | 1000 | 1100 | |
| | 120 | 1200 | 1300 | |

**Notes**

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dI/dt does not exceed 20 A/µs

(2) For voltage pulses with $t_p \leq 5$ ms

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---|---|---|---|---|---|---|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS |
| Maximum average on-state current at case temperature | $I_{T(AV)}$ | 180° conduction, half sine wave | | | 10 | A |
| | | | | | 85 | °C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | | | | 25 | A |
| Maximum peak, one-cycle non-repetitive surge current | $I_{TSM}$ | t = 10 ms | No voltage reapplied | Sinusoidal half wave, initial $T_J = T_J$ maximum | 225 | A |
| | | t = 8.3 ms | | | 240 | |
| | | t = 10 ms | 100 % $V_{RRM}$ reapplied | | 190 | |
| | | t = 8.3 ms | | | 200 | |
| Maximum $I^2t$ for fusing | $I^2t$ | t = 10 ms | No voltage reapplied | | 255 | $A^2s$ |
| | | t = 8.3 ms | | | 233 | |
| | | t = 10 ms | 100 % $V_{RRM}$ reapplied | | 180 | |
| | | t = 8.3 ms | | | 165 | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 to 10 ms, no voltage reapplied | | | 2550 | $A^2\sqrt{s}$ |
| Low level value of threshold voltage | $V_{T(TO)1}$ | (16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 1.10 | V |
| High level value of threshold voltage | $V_{T(TO)2}$ | ($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 1.39 | |
| Low level value of on-state slope resistance | $r_{t1}$ | (16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 24.3 | mΩ |
| High level value of on-state slope resistance | $r_{t2}$ | ($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum | | | 16.7 | |
| Maximum on-state voltage | $V_{TM}$ | $I_{pk}$ = 32 A, $T_J$ = 25 °C, $t_p$ = 10 ms sine pulse | | | 1.75 | V |
| Maximum holding current | $I_H$ | $T_J$ = 25 °C, anode supply 12 V resistive load | | | 130 | mA |
| Typical latching current | $I_L$ | | | | 200 | |

| SWITCHING | | | | | |
|---|---|---|---|---|---|
| **PARAMETER** | | **SYMBOL** | **TEST CONDITIONS** | **VALUES** | **UNITS** |
| Maximum rate of rise of turned-on current | $V_{DRM} \leq 600$ V | dI/dt | $T_J = T_J$ maximum, $V_{DM}$ = Rated $V_{DRM}$<br>Gate pulse = 20 V, 15 Ω, $t_p$ = 6 µs, $t_r$ = 0.1 µs maximum<br>$I_{TM}$ = (2 x rated dI/dt) A | 200 | A/µs |
| | $V_{DRM} \leq 800$ V | | | 180 | |
| | $V_{DRM} \leq 1000$ V | | | 160 | |
| | $V_{DRM} \leq 1600$ V | | | 150 | |
| Typical turn-on time | | $t_{gt}$ | $T_J$ = 25 °C,<br>at rated $V_{DRM}/V_{RRM}$, $T_J$ = 125 °C | 0.9 | µs |
| Typical reverse recovery time | | $t_{rr}$ | $T_J = T_J$ maximum,<br>$I_{TM} = I_{T(AV)}$, $t_p$ > 200 µs, dI/dt = - 10 A/µs | 4 | |
| Typical turn-off time | | $t_q$ | $T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p$ > 200 µs, $V_R$ = 100 V, dI/dt = - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM}$, gate bias 0 V to 100 W | 110 | |

**Note**

- $t_q$ = 10 µs up to 600 V, $t_q$ = 30 µs up to 1600 V available on special request

| BLOCKING | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **VALUES** | **UNITS** |
| Maximum critical rate of rise of off-state voltage | dV/dt | $T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$ | 100 | V/µs |
| | | $T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$ | 300 (1) | |

**Note**

(1) Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 10RIA120S90

| TRIGGERING | | | | | |
|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **VALUES** | **UNITS** |
| Maximum peak gate power | $P_{GM}$ | $T_J = T_J$ maximum | | 8.0 | W |
| Maximum average gate power | $P_{G(AV)}$ | | | 2.0 | |
| Maximum peak positive gate current | $I_{GM}$ | $T_J = T_J$ maximum | | 1.5 | A |
| Maximum peak negative gate voltage | $-V_{GM}$ | $T_J = T_J$ maximum | | 10 | V |
| DC gate current required to trigger | $I_{GT}$ | $T_J$ = - 65 °C | Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied | 90 | mA |
| | | $T_J$ = 25 °C | | 60 | |
| | | $T_J$ = 125 °C | | 35 | |
| DC gate voltage required to trigger | $V_{GT}$ | $T_J$ = - 65 °C | | 3.0 | V |
| | | $T_J$ = 25 °C | | 2.0 | |
| | | $T_J$ = 125 °C | | 1.0 | |
| DC gate current not to trigger | $I_{GD}$ | $T_J = T_J$ maximum, $V_{DRM}$ = Rated value | | 2.0 | mA |
| DC gate voltage not to trigger | $V_{GD}$ | $T_J = T_J$ maximum, $V_{DRM}$ = Rated value | Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated $V_{DRM}$ anode to cathode applied | 0.2 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **VALUES** | | **UNITS** |
| Maximum operating junction and storage temperature range | $T_J$, $T_{Stg}$ | | - 65 to 125 | | °C |
| Maximum thermal resistance, junction to case | $R_{thJC}$ | DC operation | 1.85 | | K/W |
| Maximum thermal resistance, case to heatsink | $R_{thCS}$ | Mounting surface, smooth, flat and greased | 0.35 | | |
| | | | **TO NUT** | **TO DEVICE** | |
| Mounting torque | | Lubricated threads (Non-lubricated threads) | 20 (27.5) | 25 | lbf · in |
| | | | 0.23 (0.32) | 0.29 | kgf · m |
| | | | 2.3 (3.1) | 2.8 | N · m |
| Approximate weight | | | 14 | | g |
| | | | 0.49 | | oz. |
| Case style | | See dimensions - link at the end of datasheet | TO-208AA (TO-48) | | |

| $\Delta R_{thJC}$ CONDUCTION | | | | |
|---|---|---|---|---|
| **CONDUCTION ANGLE** | **SINUSOIDAL CONDUCTION** | **RECTANGULAR CONDUCTION** | **TEST CONDITIONS** | **UNITS** |
| 180° | 0.44 | 0.32 | $T_J = T_J$ maximum | K/W |
| 120° | 0.53 | 0.56 | | |
| 90° | 0.68 | 0.75 | | |
| 60° | 1.01 | 1.05 | | |
| 30° | 1.71 | 1.73 | | |

**Note**

- The table above shows the increment of thermal resistance $R_{thJC}$ when devices operate at different conduction angles than DC

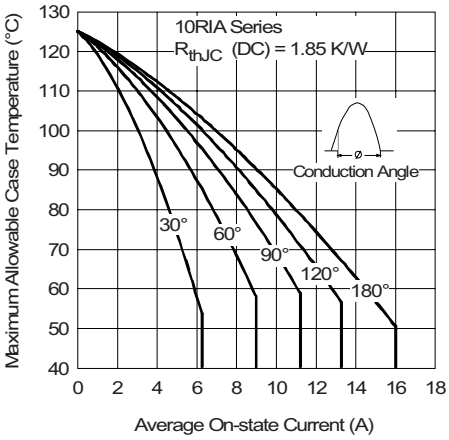


Fig. 1 - Current Ratings Characteristics

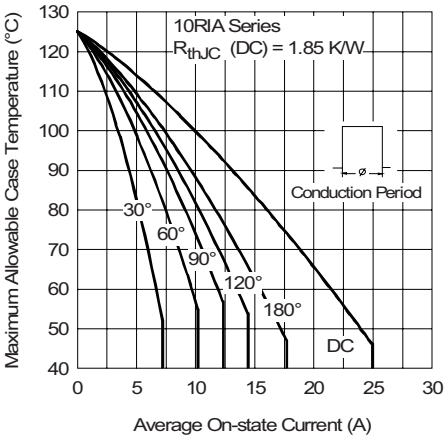


Fig. 2 - Current Ratings Characteristics

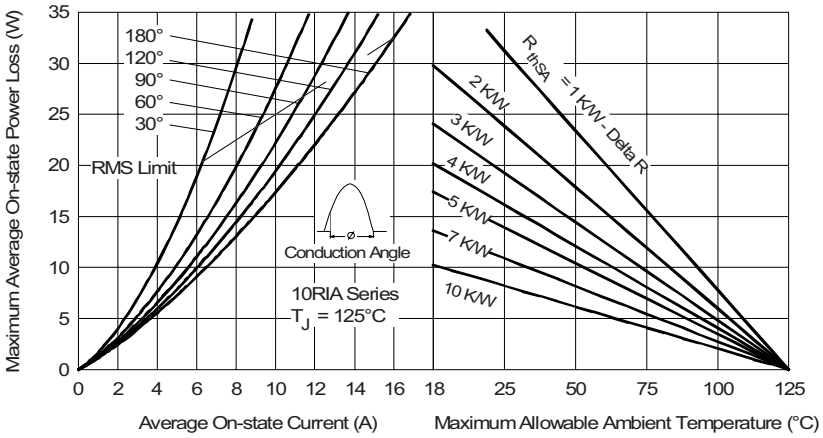


Fig. 3 - On-State Power Loss Characteristics

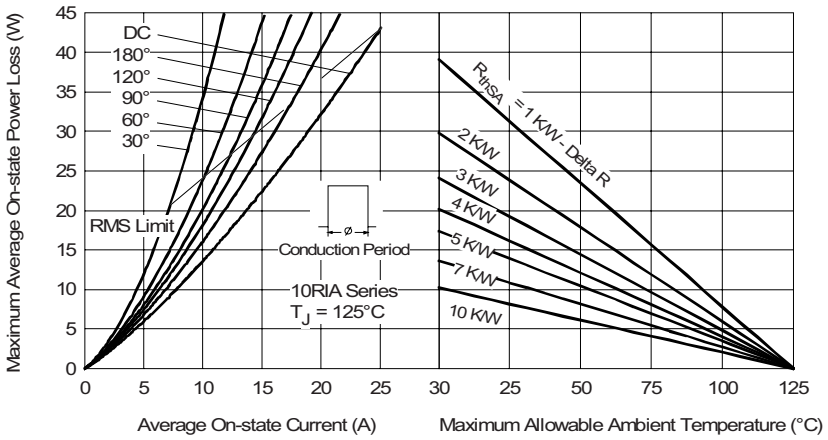


Fig. 4 - On-State Power Loss Characteristics

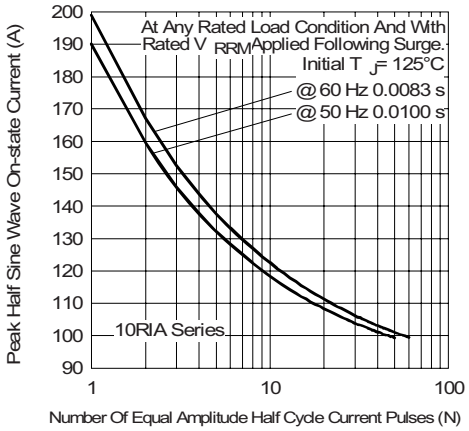


Fig. 5 - Maximum Non-Repetitive Surge Current

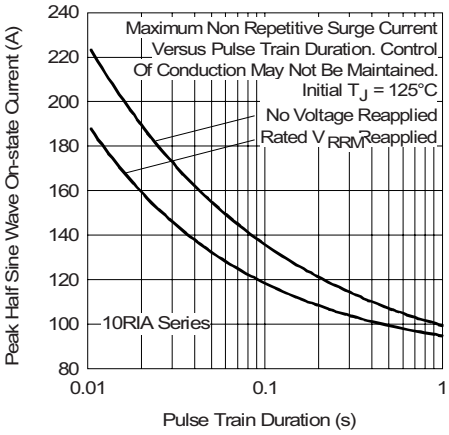


Fig. 6 - Maximum Non-Repetitive Surge Current

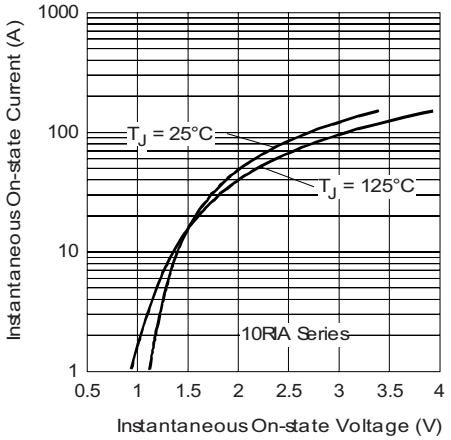


Fig. 7 - Forward Voltage Drop Characteristics

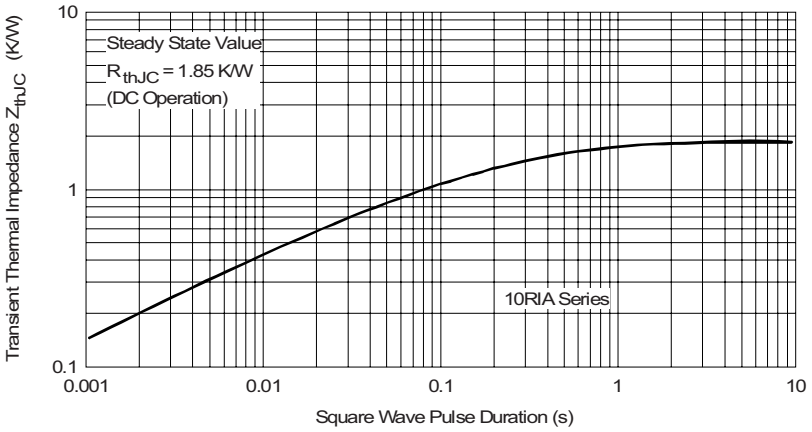


Fig. 8 - Thermal Impedance $Z_{thJC}$ Characteristics

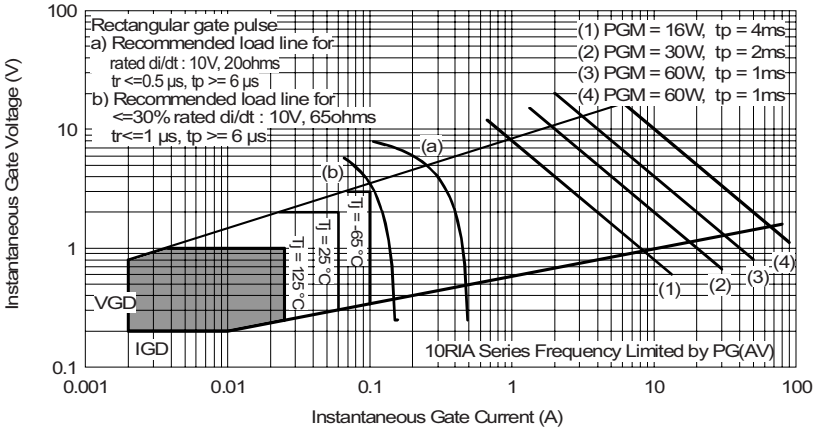


Fig. 9 - Gate Characteristics

## ORDERING INFORMATION TABLE

| Device code | 10 | RIA | 120 | M | S90 |
|---|---|---|---|---|---|
| | 1 | 2 | 3 | 4 | 5 |

1 - Current code

2 - Essential part number

3 - Voltage code x 10 = $V_{RRM}$ (see Voltage Ratings table)

4 - None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
M = Stud base TO-208AA (TO-48) M6 x 1

5 - Critical dV/dt:
None = 300 V/µs (standard value)
S90 = 1000 V/µs (special selection)

| LINKS TO RELATED DOCUMENTS | |
|---|---|
| Dimensions | http://www.vishay.com/doc?95333 |

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